

**TITLE OF THE INVENTION:**

**[0001]** WIDE COMMON MODE DIFFERENTIAL INPUT AMPLIFIER AND METHOD

**CROSS-REFERENCE TO RELATED APPLICATIONS**

**[0002]** This application claims priority from United States provisional application Serial Number 06/331,522, filed November 19, 2001, the contents of which are hereby incorporated by reference.

**BACKGROUND OF THE INVENTION:****Field of the Invention:**

**[0003]** This invention relates to an input/output (I/O) interface circuitry for high speed integrated circuit (IC) applications. More specifically, it relates to the low voltage differential signaling input buffers that have a wide common mode input range and low power consumption.

**Description of the Related Art:**

**[0004]** Differential drivers and receivers are well known. Differential drivers and receivers are used in many input/output (I/O) applications such as in communications, video and integrated circuits that may demand high data transfer rate. Differential drivers and receivers are used in integrated circuits (IC) for on-chip communications between circuits, chip-to-board, off-chip communications, etc.

**[0005]** Low-voltage differential signaling (LVDS) technology was developed in order to provide a low-power and low-voltage alternative to other high-speed I/O interfaces specifically for point-to-point transmissions, such as those used in a network devices within data and communication networks. LVDS can be

implemented in IC's to overcome some deficiencies with previous I/O interface circuitry.

**[0006]** In conventional I/O designs, high-speed data rates are accomplished with parallel I/O structures, where each I/O device typically has a limited bandwidth. As bandwidth is increased, more I/O devices are required to achieve the increased bandwidth. Over the years, bandwidth has increased substantially leading to massive parallelism in I/O designs in IC's and require more power. As a result, these parallel I/O structures occupy more and more space on IC's. This complicates the design of the circuits because there is less space available on the chip and increases the cost of such IC's because of the additional power required because of the numerous extra pads, current sources, etc. necessary in a parallel structure. Thus, most existing I/O drivers are not power efficient.

**[0007]** LVDS interfaces have reduced voltage swing and can operate at very high speed with less power consumption. With differential outputs, a LVDS receiver can reject ambient common mode noise and less parallelism is needed due to the increased data rate of LVDS I/O drivers. Thus, the use of LVDS can reduce the overall cost and size of high speed ICs.

**[0008]** However, LVDS requires a common mode input voltage that is substantially bounded by the supply voltages. This is often referred to as a rail-to-rail input voltage. In Complementary Metal-Oxide-Semiconductor (CMOS) process, two types of transistors are available for the IC design: N-type Metal-Oxide-Semiconductor (NMOS) and P-type Metal-Oxide-Semiconductor (PMOS). An NMOS transistor is turned ON when the gate voltage ( $V_g$ ) is above the source voltage ( $V_s$ ) by the threshold voltage ( $V_{tn}$ ), or when  $V_g - V_s > V_{tn}$ . Since  $V_s$  is

typically set to ground, to turn an NMOS transistor ON, it is required to have  $V_g > V_{tn}$ . If  $V_{tn}$  is in a range of 0.4V, the transistor will be OFF if the input  $V_g$  is near ground.

**[0009]** A PMOS transistor is turned ON when the gate voltage is below the source voltage ( $V_s$ ) by threshold voltage ( $V_{tp}$ ), or when  $V_s - V_g > V_{tp}$ .  $V_s$  is typically the power supply voltage, VDD. Thus to turn a PMOS transistor ON, it is required to have  $V_g < VDD - V_{tp}$ . If  $V_{tp}$  is in a range of 0.4V, the PMOS transistor will be OFF if  $V_g = VDD$ , since  $V_g > VDD - 0.4$ . Therefore, neither an NMOS nor a PMOS input stage can meet a rail-to-rail common-mode input range  $0V < V < 2.4V$ , which is specified by the LVDS standard, in IEEE Std. 1596.3-1996.

**[0010]** A prior art wide input range amplifier is shown in Fig. 5. The amplifier includes two input buffers B1 and B2, which may be implemented by a PMOS stage and an NMOS stage. The outputs of buffers B1 and B2 are combined in a MUX M1, which receives an input control signal from a Schmidt trigger ANDed with the common mode voltage  $V_{cm}$ , via a third buffer B3. The control signal Z selects which output range to use, XP or XN. This is then input into the digital logic of the circuit.

**[0011]** This prior art design is complicated and takes up much space on the chip. Furthermore, the prior art design increases power consumption necessary, therefore increasing the cost of the chip or IC.

**[0012]** In view of the deficiencies in the prior art, there is a need for new and improved systems and methods for buffering LVDS in modern I/O applications.

#### **SUMMARY OF THE INVENTION:**

**[0013]** According to an embodiment of the present invention, provide is a wide input range amplifier including a first and second stage. The first stage has first and second inputs, first and second outputs, and first, second and third voltage sources.

The first stage accepts input signals having a first common mode voltage range and outputs a first output signal having a second common mode voltage range and being amplified a first amount. The second stage has first and second inputs connected to the first and second outputs of the first stage, respectively. The second stage accepts input signals having a common mode voltage in the second range and outputs a second output signal having a third common mode voltage range and being amplified a second amount.

**[0014]** According to another embodiment of the present invention, provided is a method of buffering an input signal including steps of providing a first amplifier stage for receiving an input signal having a first voltage range, amplifying the input signal a first amount, and outputting an output signal having a second voltage range being amplified said first amount. The method further includes steps of providing a second amplifier stage for receiving the output signal from said first amplifier stage, amplifying the output signal a second amount, and outputting a differential output signal having a third voltage range being amplified said second amount.

**[0015]** According to another embodiment of the present invention, provided is a method for receiving a signal, which includes the steps of receiving a thick device signal having a first common mode range; amplifying the thick device signal a first amount and stepping the thick device signal down to a first thin device signal having a second common mode range; and amplifying the thin device signal a second amount and outputting a second thin device signal having a third common mode voltage range.

**[0016]** According to another embodiment of the present invention, provided is a wide input range amplifier which includes a first and second amplifying means. The

first amplifying means for accepting input signals having a first common mode voltage range and outputting a first output signal having a second common mode voltage range and being amplified a first amount. The second amplifying means for accepting input signals having a common mode voltage in the second range and outputting a second output signal having a third common mode voltage range and being amplified a second amount.

#### **BRIEF DESCRIPTION OF THE DRAWINGS:**

**[0017]** The objects and features of the invention will be more readily understood with reference to the following description and the attached drawings, wherein:

**[0018]** Figure 1 is a schematic of a wide input ranger amplifier according to an embodiment of the present invention;

**[0019]** Figure 2 is a schematic of a wide input ranger amplifier according to another embodiment of the present invention;

**[0020]** Figure 3 is a schematic of a wide input ranger amplifier according to another embodiment of the present invention;

**[0021]** Figure 4 is a flowchart of a method for amplifying a wide range input signal according to another embodiment of the present invention; and

**[0022]** Figure 5 is a block diagram of a prior art wide input range amplifier.

#### **DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS:**

**[0023]** In a digital CMOS process, there are two types of devices in terms of gate oxide thickness. One is called a thick device and has a high threshold voltage, and another is called a thin device and has a low threshold voltage. For an example, in the 0.13 $\mu$  digital process there are 2.5V and 1.2V devices. Thick devices are ideal for

sustaining high voltage in the interface circuitry, and thin devices with low threshold devices are preferred for their high speed and lower power consumption, for digital core circuitry. Thus, one function of an LVDS input buffer (receiver) is to accept a voltage signal from outside the chip or IC, and convert the signal to 1.2V logic for core processing.

**[0024]** In single ended input buffer, it is well known that duty cycle distortion can occur if rising and falling edges are not the same. This is more important in high speed data applications, where the distortion in the range of pico seconds are counted. Differential output can reduce duty cycle distortion. Thus, for high speed application, an LVDS buffer with a differential output is desired. This patent describes an LVDS input buffer with wide common-mode input range, low duty cycle distortion, and low power consumption.

**[0025]** Fig. 1 shows a two-stage wide common mode input buffer schematic. The buffer includes a pre-amplifier 10 stage and a Current Mode Logic (CML) stage 20. A first source voltage VDD1 is a 2.5V I/O voltage (thick device), and a second source voltage VDD2 is 1.2V core voltage (thin device) used for the digital core. A common mode voltage source Vcm is ideally set to  $(VDD1)/2$ , but in this case it can be 1.2V for practical reasons.

**[0026]** The pre-amp stage 10 includes complementary input stages. In this embodiment, a first PMOS stage (106 and 108) and a second NMOS stage (110 and 112) are used. By applying complementary stages at the input stage, the input buffer can accept wide input common voltages.

**[0027]** NMOS transistor 104 provides bias current to NMOS transistors 110 and 112. NMOS transistor 104 has its gate tied to a bias control voltage 116. The gain that is generated by NMOS transistor 110 may be given by the formula:

**[0028]**  $G_m(110) \cdot R(118),$

**[0029]** where  $G_m(110)$  is the transconductance of NMOS transistor 110, and  $R(118)$  is the resistance of load resistor 118. Note, in a typical design, NMOS transistors 110 and 112 may have the same size and characteristics. Similarly, PMOS transistors 106 and 108, also have the same size and characteristics. Load resistors 118 and 120 act as load resistors and preferably have the same resistance. The current source is provided by PMOS 102, which has its gate tied to a bias control voltage 114.

**[0030]** CML stage 20 may be a differential amplifier and include a PMOS output stage. The gain generated by the CML PMOS stage is given by  $G_m(106) \cdot R(118)$ , where  $G_m(106)$  is the transconductance of transistor 106. Since the outputs of the NMOS and PMOS stage are combined at node 260 and 261, the overall differential gain is given by the equation:

**[0031]**  $A_D = [G_m(110) + G_m(106)] \cdot R(118).$

**[0032]** Since the output is differential, the duty cycle can be better maintained. Incoming data is supplied to input nodes  $V_{inP}$  and  $V_{inN}$ .

**[0033]** Common mode voltage  $V_{cm}$  is typically set to a voltage near the middle of voltage source  $V_{DD1}$ . The input range is limited by the common mode voltage  $V_{cm}$ . In a case when  $V_{inP}$  and  $V_{inN}$  are quite high (e.g., 1.8V-2.4V), both PMOS transistors 106 and 108 tend to be OFF. However, the NMOS stage, NMOS transistors 110 and 112 will be ON. Similarly, when the input voltages  $V_{inN}$  and  $V_{inP}$

are both low, then both NMOS transistors 110 and 112 are OFF, and PMOS transistors 106 and 108 will remain ON

**[0034]** Accordingly, complementary input stages achieve a wide common mode input voltage range. Although, the common-mode input range is not rail-to-rail, this embodiment of the present invention provides a simple and low cost (i.e., smaller in size and takes up less silicon area) wide input range solution.

**[0035]** In the second stage of the input buffer, Current Mode Logic 20, a current sink (source) is provided by an NMOS transistor 204, which is biased by a bias voltage 117. One having ordinary skill in the art will readily understand how to bias NMOS transistor 204 in a CML stage. NMOS transistors 210 and 212 provide a differential gain which can be calculated by:

**[0036]**  $Gm(210) * R(220)$

**[0037]** to the output nodes Vout1 and Vout2; where Gm(210) is the transconductance of transistor 210, and R(220) is the resistance of resistor 220. The second stage, CML stage 20, completes the voltage level shift from VDD1 to VDD2, at which the digital core operates.

**[0038]** Fig. 2 shows the schematic of a differential receiver pre-amp with rail-to-rail common mode input range according to another embodiment of the present invention. Pre-amp 300 uses cascoded structures to fold the gain to differential resistors. To produce a wide-range differential receiver, the second stage can be a CML stage or differential amplifier, such as CML 20, shown and described with reference to Fig 1.

**[0039]** Similar to the pre-amp 10 of Fig. 1, pre-amp 300 includes a complementary input pair, NMOS input stage (110 and 112) and PMOS input stage



(106 and 108). Pre-amp 300 includes a current source, NMOS transistor 104 which provides bias current to the input NMOS transistor pair 110 and 112. The gate of the transistor 104 is controlled by bias control voltage 316. The inputs to the pre-amplifier 300 are  $V_{inp}$  and  $V_{inn}$ , and are connected to the gates of the input NMOS transistor pair 110 and 112 and to the gates of PMOS transistor pair 106 and 108. PMOS transistors 302 and 304 are current sources which provide proper bias current to PMOS transistors 306 and 308. The gates of transistor 306 and 308 are controlled by another bias voltage 318. The input NMOS pair 110 and 112 drive the differential resistors 118 and 120 through the cascoded transistors 306 and 308, which are cascoded with NMOS transistors 110 and 112, respectively. The load resistors 118 and 120 are also loaded to a common mode voltage  $V_{cm}$ . The common mode voltage may be set to near the middle of the supply voltage  $V_{DD1}$  or  $V_{DD1}/2$ . For practical reasons,  $V_{cm}$  may be set to  $V_{DD2}$ . The differential gain of this NMOS stage provides voltage gain of  $G_m(110) \cdot R(120)$ , at output nodes  $Outp$  and  $Outn$ .

**[0040]** In a typical application, preamplifier 300 includes NMOS transistors 110 and 112 which can have the same size and characteristics, as do PMOS transistors 306 and 308, PMOS transistors 302 and 304, and differential resistors 118 and 120.

**[0041]** Similar to the NMOS input pair, the input PMOS pair 106 and 108 drive the differential resistors 118 and 120 through the cascaded NMOS transistors 310 and 312, where transistor 310 and 312 are biased from voltage 320. The bias current for the tail current 104 (current sink) is controlled by a bias voltage 316. Transistors 310 and 312 receive bias current from NMOS transistors 314 and 315, respectively. The differential gain of this stage is given by  $G_m(106) \cdot R(118)$  at nodes  $Outn$  and  $Outp$ . In

a typical application, transistors 106 and 108 have the same size and characteristics, as do transistors 310 and 312, and transistors 314 and 315. Since the output of NMOS stage and PMOS stage are combined at nodes Outn and Outp, the gain ( $A_v$ ) for the PMOS stage and NMOS stage can be summed by the equation:

**[0042]** 
$$A_v = [G_m(110) + G_m(106)] * R(118).$$

**[0043]** However, the gain will depend on the input common mode range. When input voltages are near the supply voltage, only NMOS transistor pair (110, and 112) is ON, and the differential gain is reduced to

**[0044]** 
$$G_m(110) * R(118),$$

**[0045]** since not current in 106 and 108 and  $G_m(106)=0$ . When input common mode is very low or near ground, only PMOS transistor pair (106 and 108) will be ON. The gain may be given by

**[0046]** 
$$A_D = G_m(106)*R(118),$$

**[0047]** since  $G_m(110)=0$ .

**[0048]** The common mode input voltage range can be designed in the following manner. When the inputs  $V_{inp}$  and  $V_{inn}$  are very high, only NMOS transistor pair 110 and 112 will be ON. To have NMOS transistors 110 and 112 in the saturation region, it is required to maintain:

**[0049]** 
$$V_d(110) - V_s(110) > V_g(110) - V_s(110) - V_{tn},$$

**[0050]** where  $V_d(110)$  is the drain voltage (all referenced to ground ( $V_{SS}$ )) for NMOS 110,  $V_s(110)$  is the source voltage,  $V_g(110)$  is the gate voltage, and  $V_{tn}$  is the threshold voltage of the NMOS transistor. Thus, to achieve an input range as high as  $V_{DD1}$ , i.e.,  $V_g=V_{DD1}$ , transistors 306 and 308 should be biased through the bias voltage 318, so that  $V_d$  of transistors 110 and 112 are greater than  $(V_{DD1}-V_{tn})$ .

**[0051]** When the input is low (i.e., near ground), only transistors 106 and 108 will be ON. To maintain the transistor pair 106 and 108 in the saturation region, it is required to maintain:

**[0052]**  $V_s(106) - V_d(106) > V_s(106) - V_g(106) - V_{tp},$

**[0053]** where  $V_s(106)$  is the source voltage referenced to ground VSS,  $V_d(106)$  is the drain voltage,  $V_g$  is the gate voltage, and  $V_{tp}$  is the threshold voltage for PMOS transistor 106. At worst, when input is as low as VSS,  $V_g(106) = 0$ , and  $V_d(106)$  must be less than  $V_{tp}$ . This can be met by bias transistor 310 and 312 through the bias voltage 320.

**[0054]** Fig. 3 shows another embodiment of a pre-amplifier with rail-to-rail common mode input voltage range according to the present invention. Similar to the embodiment of Fig. 2, the second stage of the amplifier can be a current mode logic CML stage or differential amplifier as shown and described with reference to Fig. 1. The embodiment is very similar to the embodiment of Fig. 2. The main difference from the schematic of Fig. 2 is that the current source transistors 302, 304, 314, and 315 are replaced with resistors 402, 404, 406, and 408. The operation of the circuit is very similar to that in Fig. 2, but the overall gain is reduced since the resistors 402-408 introduce load on the input pairs. In a typical implementation, the resistance of resistors 402-408 may be equal. When the resistance of resistor 402 is significantly greater than  $1/G_m(306)$  and the resistance of resistor 404 is significantly greater than  $1/G_m(308)$  (the transconductor of transistor 308), the voltage gain will be close to

**[0055]**  $A_v = [G_m(110) + G_m(106)] * R(118)$

**[0056]** Thus, according to the present invention, provided are a wide input stage buffers which perform level shifting from a high (I/O voltage) voltage to low voltage (digital core voltage). The buffer of the present invention includes a pre-amp stage and a differential amplifier stage. The differential output reduces duty cycle distortion. The wide input range pre-amp stages use complementary input pairs to accept wide input ranges. Cascoded stages may be used to improve input range.

**[0057]** Fig. 4 is a flowchart of a method for receiving a wide input range input signal and stepping it to core voltage according to an embodiment of the present invention. The process begins at step S5-1. At step S5-2, a pre-amplifier (first stage) including complementary input stages, is provided. At steps S4-3 and S4-4, the complementary input stages may be configured such as described above with references to Figs. 1-3. For example, the input stages may include a PMOS pair and an NMOS pair, only one of which will be on for a given voltage range. Each transistor of the input pairs may be cascoded in order to fold the gain to load resistors, as described with reference to Figs. 2-3. The pre-amplifier stage may be configured to provide a gain to an input signal and also to reduce the common mode voltage range, so that an amplified output signal may be output at step S4-5 having an improved voltage range. The input signal may be within the LVDS standard range.

**[0058]** Next, at step S4-6, a second stage amplifier may be provided to receive the output signal from the first stage amplifier, and may be configured as described in Fig. 1. The second stage amplifier may be designed to step the signal down for use in the digital core, and reduce the common mode voltage range to a negligible range for output at step S4-7. As already described above, this can be accomplished with a CML differential amplifier.

**[0059]** Note that the above-described flow chart is merely exemplary and describes a method for buffering an input signal or for providing a wide common mode differential receiver. One having ordinary skill in the art will readily understand that the steps may be performed in a separate order or all at the same time.

**[0060]** Thus, the present invention has been fully described with reference to the drawing figures. Although the invention has been described based upon these preferred embodiments, it would be apparent to those of skilled in the art that certain modifications, variations, and alternative constructions would be apparent, while remaining within the spirit and scope of the invention. In order to determine the metes and bounds of the invention, therefore, reference should be made to the appended claims. For example, the differential resistor load can be replaced with active transistor loads or other equivalent loads.